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## THE FREE RUNNING MULTIVIBRATOR

by

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#### THE FREE RUNNING MULTIVIBRATOR

These notes were written as a guide for the design of a widely used transistor circuit – The Free Running Multivibrator. Limiting values for the resistors are obtained through simple static calculation of the bias conditions for a given temperature range.

The important advantages to be derived from this improved circuit are greater starting reliability and distinctly faster rise time.

This application note is being distributed in connection with the release and immediate availability of the Raytheon 2N 438, 2N 439, and 2N 440 Germanium fusion alloy NPN transistors designed for use in computers and switching applications where reliability is a primary consideration.

#### A. CONVENTIONAL CIRCUIT:

A conventional circuit for a saturating free running multivibrator is shown in Figure 1.



FIGURE 1

A disadvantage of this circuit is the long rise time, which can easily be explained as follows:

Suppose  $T_1$  conducting,  $T_2$  cutoff. The collector-emitter voltage of  $T_1$  has then the saturation value  $V_s$ . As soon as the base of  $T_2$  has a forward bias  $V_b$ ,  $T_2$  comes into conduction. At this moment the voltage across  $C_1$  equals  $(V_b - V_s) = 0.1V$  so that  $C_1$  is practically completely discharged. As  $T_1$  goes out of conduction,  $C_1$  is recharged via  $R_L$  so that the collector voltage  $V_c$  of  $T_1$  will rise exponentially toward +E. Neglecting the input resistance of  $T_2$ ,  $V_c$  is given by:

$$V_{c} = E \begin{pmatrix} -t/R_{L}C_{l} \\ 1 - e \end{pmatrix}$$
(1)

The rise time is then found to be:

 $tr = R_L C_1 \ln 10 = 2.3 R_L C_1$ 

An approximate formula for the period T is:

$$T = (R_1 C_1 + R_2 C_2) \ln 2$$

or if  $R_1 C_1 = R_2 C_2$ :

$$T = 2 \ln 2 (R_1 C_1)$$

Combining:

$$\frac{\mathrm{tr}}{\mathrm{T}} = \frac{\mathrm{ln}\ 10}{2\ \mathrm{ln}\ 2} \left( \frac{\mathrm{R}_{\mathrm{L}}}{\mathrm{R}_{\mathrm{I}}} \right) = -1.66 \left( \frac{\mathrm{R}_{\mathrm{L}}}{\mathrm{R}_{\mathrm{I}}} \right) \tag{2}$$

Saturation requires that  $R_1 < hFE R_L$ 

so that:

$$\frac{\mathrm{tr}}{\mathrm{T}} > \frac{1.66}{\mathrm{hFE}} \tag{3}$$

If the circuit is designed for a minimum hFE of 40 then tr/T = 4%. At 1 kcs this would mean a rise time of 40  $\mu$  sec.

Another disadvantage of this circuit is the possibility that  $T_1$  and  $T_2$  go both into saturation so that the circuit does not always start oscillating when switched on.

#### B. ALTERNATE CIRCUIT

A very satisfactory circuit is shown in Figure 2.





Initially both  $T_1$  and  $T_2$  are conducting, there is no charge on C. The proportioning of voltage and resistor values is such that there is no saturation under these conditions.

Since the loop gain is greater than unity, this situation is unstable. As a result, the emitter voltage of  $T_2$  will rise, causing  $T_1$  to cut off and base and emitter of  $T_2$  will rise further until they are limited by the supply voltage.

C is now charged via  $R_2$  and  $T_2$ .

Since  $V_b$  is fairly constant during the process, the drop of  $V_b$  is compensated by the initial charge on C equivalent to  $V_b$ , and  $V_b$  may be neglected here.

The resistor  $R_1$  is equivalent to a resistor  $R_1/h_{FE2}$  in the emitter lead and can be neglected in most cases.

The charging voltage is  $(E_1 + E_2)$  and the charging ends when the voltage across  $R_2$  equals  $(E_2 - V_b)$ , when  $T_1$  takes over.

Thus the charge time is:  $t_1 = R_2 C \ln \left(\frac{E_1 + E_2}{E_2 - V_b}\right)$ 

Now  $T_1$  is conducting and  $T_2$  is cut off. C is discharged via  $R_3$  and  $T_1$ .

The discharge time is the time required for the voltage across  $R_3$  to drop from  $(E_1 + E_2 - V_b)$  to  $(E_2 - 2 V_b)$ .

$$t_2 = R_3 C \ln \left( \frac{E_1 + E_2 - V_b}{E_2 - 2V_b} \right)$$
 (5)

And the total period:  $T = R_2 C \ln \left( \frac{E_1 + E_2}{E_2 - V_b} \right) + R_3 C \ln \left( \frac{E_1 + E_2 - V_b}{E_2 - 2V_b} \right)$  (6)

### CALCULATION OF $R_1$ :

 $R_1$  can be calculated from the saturation conditions for  $T_1$ .

A maximum value can be found from the requirement that  $T_1$  should not be saturated under static conditions.

The result is: 
$$R_1 < \left(\frac{E_1 + V_b}{E_2 - V_b}\right) R_2$$
(7)

For a good wave-shape it is however required that  $T_1$  be saturated under dynamic conditions.

Therefore: 
$$I_{c1} R_1 = E_1$$

or if we assume  $\alpha = 1$ 

 $I_{e1} R_1 = E_1$ 

Under dynamic conditions,  $I_{e1}$  is increased by the discharge current  $I_d$ .

 $I_d$  decreases exponentially from  $I_{d1}$  at the beginning to  $I_{d2}$  at the end of the discharge period, where

$$I_{d1} = \frac{E_1 + E_2 - V_b}{R_3}$$
$$I_{d2} = \frac{E_2 - 2V_b}{R_3}$$

Adding the static value of  $I_{e1}$ ,  $\frac{(E_2 - V_b)}{R_2}$ , the following relationship is obtained.

$$\frac{E_2 - V_b}{R_2} + \frac{E_1 + E_2 - V_b}{R_3} > I_{e1} > \frac{E_2 - V_b}{R_2} + \frac{E_2 - 2 V_b}{R_3}$$
(8)

Taking the minimum value of  $I_{e1}$ , a minimum value for  $R_1$  is found, so that

$$R_{1} > \frac{E_{1}}{E_{2} - V_{b}} + \frac{E_{2} - 2V_{b}}{R_{3}}$$

A complication arises however, since the process described above will repeat only if the loop gain is greater than unity at the end of the cycle. This requires that  $T_1$  is not saturated. For this reason it is advisable to choose R1 equal to the minimum value of (9).

Example:

$$E_1 = 4.5V$$
 $T_1$ Raytheon NPN units (such as 2N440) $E_2 = 1.5V$  $T_2$  $h_{FE} = 100$  $V_b = 0.2V$ Alpha Cutoff = 11 mcs

Of all three resistors one can be chosen, the two others can be found from conditions (9) and the equality of  $t_1$  and  $t_2$ .

In this example we will choose  $R_2 = 150$ .  $R_3$  can be found by equating (4) and (5).

$$\mathbf{R}_{2} \ln \left( \frac{\mathbf{E}_{1} + \mathbf{E}_{2}}{\mathbf{E}_{2} - \mathbf{V}_{b}} \right) = \mathbf{R}_{3} \ln \left( \frac{\mathbf{E}_{1} + \mathbf{E}_{2} - \mathbf{V}_{b}}{\mathbf{E}_{2} - 2\mathbf{V}_{b}} \right)$$

which gives  $R_3 = 138 \Omega$ 

Substituting the values of  $R_2$  and  $R_3$  in (9) yields:

 $R_1 = 271 \Omega$ 

Finally (6) gives T = 459 C seconds where C is stated in farads.

Figure 3 gives the measured period T vs capacitance.\* As can be seen, the measured curve lies almost entirely  $0.65 \,\mu$  sec higher than the calculated curve. The discrepancy is due to finite switching times and storage effects, which have been neglected in the calculations.

Also it shows that the curve shifts up with temperature. From  $-50^{\circ}$ C to  $+70^{\circ}$ C it shifts from 0.5 to 0.85  $\mu$ sec above the calculated curve. This is approximately 3 m $\mu$ sec/ $^{\circ}$ C.

\* Using the circuit of Figure 2 and the resistor values as calculated in this example.



FIGURE 3